

# 1.5A Dual High-Speed Power MOSFET Drivers

#### **Features**

- High Peak Output Current: 1.5A
- Wide Supply Voltage Operating Range: 4.5V to 24V
- High Capacitive Load Drive Capability
   1000pF in 11ns (typical)
- Short Delay Times: 35ns (typical)
- Matched Rise/Fall Times
- Low Output Impedance
- Low Supply Current
- Over-temperature Protection
- Under-voltage Lockout
- Non-overlapped Drive Tech
- ESD Protected: 2.0kV
- Input withstands negative inputs up to 5V
- Available in Green SOP8, DIP8 and DFN8
   Packages

## **Applications**

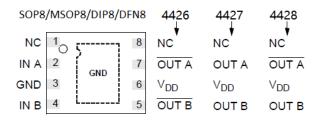
- Wireless Power Transmitter
- Switch Mode Power Supplies
- Power MOSFET Drivers
- Pulse Transformer Drivers
- Line Drivers
- CCD Driver
- Class D Switching Amplifiers

Rev1.0 Copyright@2018 Cosine Nanoelectronics Inc. All rights reserved

### **General Description**

The COS4426/7/8 are matched dual power drivers. Unique circuit MOSFET design enables high speed operation capable of delivering peak currents of 1.5A into 1000pF capacitive loads. Improved speed and drive capability are enhanced by matched rise and fall delay times. These matched delays the maintain integrity of input-to-output pulse-widths to reduce timing errors and clock skew problems. Dynamic switching losses are minimized with non-overlapped drive techniques. These devices are highly latch-up resistant within their power and voltage ratings. They are not subject to damage when up to 5V of noise spiking (of either polarity) occurs on the ground pin. All terminals are fully protected against Electrostatic Discharge (ESD) up to 2.0 kV.

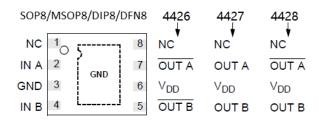
## **Pin Configuration**



COS4426: Outputs out of phase with inputs
COS4427: Outputs in phase with inputs
COS4428: OutputA: out of phase with inputA
OutputB in phase with inputA



### 1. Pin Configuration and Functions



Pin Description

Pin	Name	Description
1	NC	No connection
2	IN A	Input A
3	GND	Ground
4	In B	Input B
5	OUT B	Output of Channel B
6	VDD	Power Supply
7	OUT A	Output of Channel A
8	NC	No connection
-	PAD	Exposed Metal Pad

#### **Function Table**

		cos	4426	cos	4427	cos	4428
INA	INB	<del>OUTA</del>	OUT B	OUTA	OUTB	OUTA	OUTB
L	L	Н	Н	L	L	Н	L
L	Н	Н	L	L	Н	Н	Н
Н	L	L	Н	Н	L	L	L
Н	Н	L	L	Н	Н	L	Н
Floating	Floating	L	L	L	L	L	L

#### 1.1 Inputs A and B

MOSFET driver inputs A and B are high-impedance, TTL/CMOS compatible inputs. These inputs also have 300 mV of hysteresis between the high and low thresholds that prevents output glitching even when the rise and fall time of the input signal is very slow.

#### 1.2 Ground (GND)

Ground is the device return pin. The Ground pin(s) should have a low-impedance connection to the bias supply source return. High peak current flows out the Ground pin(s) when the capacitive load is being discharged.



#### 1.3 Output A and B

MOSFET driver outputs A and B are low-impedance, CMOS push-pull style outputs. The pull-down and pullup devices are of equal strength, making the rise and fall times equivalent.

#### 1.4 Supply Input (VDD)

The VDD input is the bias supply for the MOSFET driver and is rated for 4.5V to 24V with respect to the Ground pin. The VDD input should be bypassed with local ceramic capacitors. The value of these capacitors should be chosen based on the capacitive load that is being driven. A value of 1.0  $\mu$ F is suggested.

#### 1.5 Exposed Metal Pad

The exposed metal pad of the DFN-S package is not internally connected to any potential. Therefore, this pad can be connected to a ground plane or other copper plane on a Printed Circuit Board (PCB), to aid in heat removal from the package.

### 2. Product Specification

#### 2.1 Absolute Maximum Ratings (1)

Parameter	Min	Max	Unit
DC supply voltage Vs		28	V
Operating junction temperature	-40	125	°C
Storage temperature	-55	150	°C
Maximum input voltage	GND-5	VDD+0.3	V
Combined peak output current		4	Α

<sup>(1)</sup> Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

#### 2.2 Thermal Data

Parameter	Rating	Unit
Package Thermal Resistance	155(SOP8) 125(DIP8) 118(FDN8,2x2)	°C/W

### 2.3 Recommended Operating Conditions

Parameter	Rating	Unit
DC Supply Voltage	4.5V ~ 24V	V
Operating ambient temperature	-40 to +85	°C



#### 2.4 Electrical Characteristics

(Typical values are tested at T<sub>A</sub>=25 °C, V<sub>DD</sub>=18V)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
INPUT				<u> </u>		
Input Signal High Threshold	V <sub>IH</sub>		1.6			V
Input Signal Low Threshold	VIL				0.7	V
Input Signal Hysteresis	V <sub>HYS</sub>			0.3		V
Input Signal High Current	Іін	Inverting Input Current, V <sub>INX</sub> =18V			0.01	μA
input Signal High Current	ПН	Non-inverting Input Current, VI <sub>NX</sub> =18V		88	125	μΛ
		Inverting Input Current, V <sub>INX</sub> =0V		88	125	
Input Signal High Current	I <sub>IL</sub>	Non-inverting Input Current, V <sub>INX</sub> =0V		0.0		μA
OUTPUT						
Pull-Up Resistance	Rон	Source Current = 10mA		2.0		Ω
Pull-Down Resistance	RoL	Sink Current = -10mA		2.0		Ω
	Ірк	Source Current, f=1kHz, C <sub>L</sub> =0.1uF		2		_
Peak Output Current		Source Current, f=1kHz, C <sub>L</sub> =0.1uF		-2		A
Continuous Output Current	IDC	Source / Sink Current		±200		mA
POWER SUPPLY				•		
		Input Floating, COS4426		0.97		
Power Supply Current	Icc	Input Floating, COS4427		0.53		mA
		Input Floating, COS4428		0.75		
Operating Voltage Range	V <sub>DD</sub>		4.5		24	V
Under-Voltage Lockout ON Threshold				3.6	4	V
Under-Voltage Lockout Hysteresis				0.5		V
SWITCHING CHARACTERIS	STICS					
Rise Time	t <sub>R</sub>	CL =1000pF, See Figure 3.1		11		ns
				<u> </u>	1	1



### COS4426/4427/4428

Fall Time	t⊧	CL =1000pF, See Figure 3.1		11		ns
Turn On Delay Time	t <sub>⊡1</sub>	Non-inverting Input		34		ns
Turn-On Delay Time		Inverting Input		44		ns
Turn On Delay Time	t <sub>D2</sub>	Non-inverting Input		34		ns
Turn-On Delay Time		Inverting Input		44		ns
OVER-TEMPERATURE PROTECTION						
Thermal Shutdown Threshold				150		°C
Thermal Shutdown Threshold Hysteresis				15		°C

## 3.0 Application Information

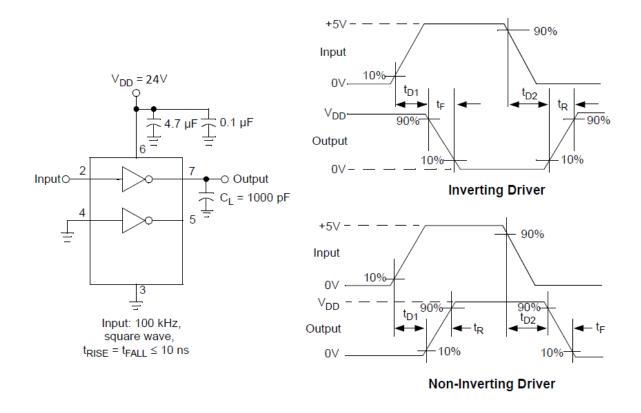
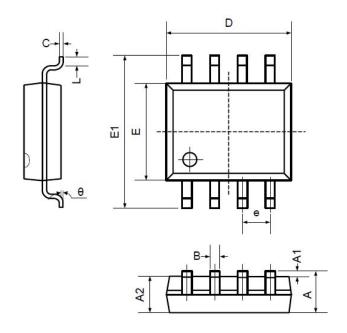


Figure 3.1 Switching Time Test Circuit



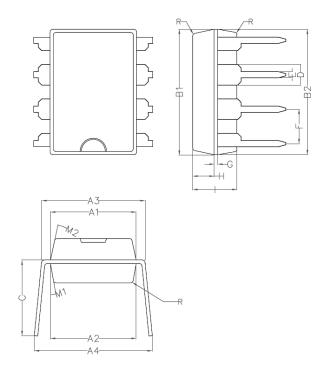
# 4.0 Package Information

## 4.1 SOP8 (Package Outline Dimensions)



Symbol		nsions meters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
В	0.330	0.510	0.013	0.020	
С	0.190	0.250	0.007	0.010	
D	4.780	5.000	0.188	0.197	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.300	0.228	0.248	
е	1.270TYP		0.050	TYP	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

## 4.3 DIP8 (Package Outline Dimensions)



Symbol	Min	Non	Max
A1	6. 28	6.33	6.38
A2	6.33	6.38	6.43
A3	7.52	7.62	7.72
A4	7.80	8.40	9.00
B1	9.15	9. 20	9. 25
B2	9.20	9. 25	9.30
С		5. 57	
D		1.52	
E	0.43	0.45	0.47
F		2.54	
G		0.25	
Н	1.54	1.59	1.64
I	3.22	3. 27	3.32
R		0.20	
M1	9°	10°	11°
M2	11°	12°	13°



# 5. Package and Ordering Information

Model	Order Number	Package	Package Option	Marking Information
COS4426	COS4426SR	SOP-8	Tape and Reel, 3000	COS4426SR
COS4426	COS4426DR	DIP-8	Tape and Reel, 1500	COS4426DR
COS4427	COS4427SR	SOP-8	Tape and Reel, 1500	COS4427SR
CO34421	COS4427DR	DIP-8	Tape and Reel, 1500	COS4427DR
COS4428	COS4428SR	SOP-8	Tape and Reel, 1500	COS4428SR
CO34426	COS4428DR	DIP-8	Tape and Reel, 1500	COS4428DR

# 单击下面可查看定价,库存,交付和生命周期等信息

>>COSINE(科山芯创)